EV318284460

Inventor:

Li Li et al.

Title:

Atomic Layer Deposition Methods of Forming Silicon Dioxide

Comprising Layers

Assignee:

Micron Technology, Inc.

INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR § 1.56. Copies of the cited art are included. No admission is made regarding whether all the submitted references are prior art.

Respectfully submitted,

Dated: 9-23-03

Attorney: Mark S. Matkin

Reg. No. 32,268

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO. MI22-2144

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	AB	2001/0041250 A1	11/15/01	Werkhoven et al.						
	AC	10/133,947		Vaartstra (as filed)				04/25/	04/25/2002	
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